

Properties of p-Copper-Indium-disulfide(CuInS_2) Thin Films by Solution Based Deposition Methods for Solar Cell Application

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We have successfully obtained Copper-Indium-disulfide(CuInS_2) thin films through the modified solution based deposition processes such as spin-CFR(continuous flow reactor), spin-SILAR(successive ionic layer adsorption and reaction), spin-spray method, respectively. The optical band gap is about 1.5eV that is suitable for the photo voltaic (PV) devices. And the structural properties of CIS thin film showed representative directions which are (112),(200), (220),(312), respectively.